

PTO 1449 (modified)

ATTY DOCKET NO.  
03500.010530.5

APPLICATION NO.

10/085,046

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)  
(Use several sheets if necessary)

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL.

FILING DATE

March 1, 2002

GROUP

2823  
2815

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
G	4,116,751	09/26/78	Zaromb	156	600		
	4,727,047	02/23/88	Bozler, et al.	437	89		
	5,248,621	09/28/93	Sano	437	3		
	5,250,460	10/05/93	Yamagata, et al.	437	62		
	5,277,748	01/11/94	Sakaguchi, et al.	156	630		
	5,278,092	01/11/94	Sato	437	90		
	5,278,093	01/11/94	Yonehara	437	109		
	5,285,078	02/08/94	Mimura, et al.	257	3		
	5,290,712	03/01/94	Sato, et al.	437	24		
	5,320,907	06/14/94	Sato	428	446		
	5,331,180	07/19/94	Yamada, et al.	257	3		
	5,362,683	11/08/94	Takenaka et al.	437	226		
	5,363,793	11/15/94	Sato	117	2		
	5,371,037	12/06/94	Yonehara	437	86		
	5,374,564	12/20/94	Bruel	437	24		
	5,403,771	04/04/95	Nishida, et al.	437	89		
	5,433,168	07/18/95	Yonehara	117	90		
	5,453,394	09/26/95	Yonehara, et al.	437	62		
	5,457,058	10/10/95	Yonehara	437	24		
	5,459,081	10/17/95	Kajita	437	3		
F	5,466,631	11/14/95	Ichikawa, et al.	437	62		
EXAMINER FOURSON			DATE CONSIDERED 5/29/04				

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				FILING DATE March 1, 2002		GROUP 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G		5,536,361	07/16/96	Kondo et al.	156	630.1	
		5,644,156	07/01/97	Suzuki, et al.	257	485	
		5,670,411	09/23/97	Yonehara, et al.	437	62	
		5,811,348	09/22/98	Matsushita, et al.	438	455	
		5,854,123	12/29/98	Sato, et al.	438	507	
		5,856,229	01/05/99	Sakaguchi, et al.	438	406	
		5,863,830	01/26/99	Bruel, et al.	438	478	
		5,869,387	02/09/99	Sato, et al.	438	459	
		5,970,361	10/19/99	Kumomi, et al.	438	409	
		5,980,633	11/09/99	Yamagata, et al.	117	94	
		6,103,598	08/15/00	Yamagata, et al.	438	459	
		6,107,213	08/22/00	Tayanaka	438	762	
		6,121,117	09/19/00	Sato, et al.	438	459	
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
G	EP	0417838 A1 ✓	09/06/90	EPO			
	EP	0469630 A2 ✓	02/05/92	EPO			
	EP	0499488A2 ✓	02/14/92	EPO			
	EP	0536790 A2 ✓	04/14/93	EP			
	EP	0553852 A2 ✓	08/04/93	EPO			
	EP	0553859 A3 ✓	08/04/93	EPO			
EXAMINER Ferguson				DATE CONSIDERED 5/29/04			

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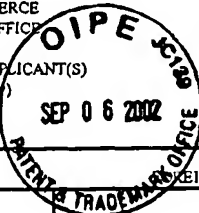
10/085,046

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL.

FILING DATE

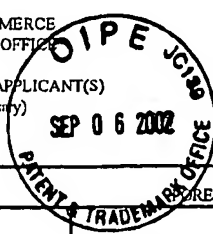
March 1, 2002


 GROUP 27  
 2813 2002

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO OR ABSTRACT
G	EP	0553860 A2 ✓	08/04/93	EPO			
	EP	0554795 A1 ✓	08/93	EPO			
	EP	0584777 A1 ✓	02/02/94	EPO			
	EP	0618624 A2 ✓	10/05/94	EPO			
	EP	0757377 A2 ✓	02/05/97	EPO			
	EP	0793263 A2 ✓	09/97	EPO			
	EP	0797258 A2 ✓	09/24/97	Europe			
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	JP	60 196955A ✓	10/05/85	Japan			Abstract
	JP	62-108539 ✓	05/19/87	Japan			Abstract
	JP	62-279625 ✓	12/04/87	Japan			Part Tran.
	JP	03-70156 ✓	03/26/91	Japan			Abstract
	JP	05-211128 ✓	08/20/93	Japan			Abstract
	JP	05-283722 ✓	10/29/93	Japan			Translation
	JP	06-45622 ✓	02/18/94	Japan			Translation
	JP	07-79016 ✓	03/20/95	Japan			Abstract
	JP	07-211602 ✓	08/11/95	Japan			Abstract
	JP	07-302889 ✓	11/14/95	Japan			Abstract
G	JP	07-326719 ✓	12/12/95	Japan			Abstract
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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT	
G	JP	9-162090	06/20/97	Japan			Abstract
G	WO	92/09104	05/29/92	PCT			
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G	✓ T. Ahe et al. "Silicon Kesshou to Doping (Silicon Crystal and Doping)", Maruzen Co., Ltd., 1986 (with partial translation)						
	✓ K. Barla, et al., "SOI Technology Using Buried Layers of Oxidized Porous Si", pp. 11-15 (1987)						
	✓ H. Baumgart, et al., "Light Scattering Topography Characterization Of Bonded SOI Wafers", Extended Abstracts, Elect. Chem. Soc. 1 <sup>st</sup> Symp., pp. 375-85 (1991)						
	✓ G.W. Cullen, ed., Journal of Crystal Growth, vol. 63, no. 3, pp. 429-590, Oct. 1993 (see p. 547.)						
	✓ Extended Abstracts (the 57 <sup>th</sup> Autumn Meeting, 1996); The Japan Society of Applied Physics (Abstr. 8a-V-8) (with translation)						
	✓ Extended Abstracts (The 44 <sup>th</sup> Spring Meeting, 1997); The Japan Society of Applied Physics and Related Societies (Abstr. 31a-B-5) (with translation)						
	✓ Extended Abstracts (The 59 <sup>th</sup> Autumn Meeting, 1998); The Japan Society of Applied Physics (Abstr. 15a-YB-4) (with translation)						
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	✓ Y. Hashimoto, "Shin-Kagaku Yougo Jiten" (new chemical term dictionary), Sankyo Shuppan Co., Ltd., 6 <sup>th</sup> Edn (1973) (definition of anodic oxidation) (with translation)						
	✓ R.P. Holmstrom, "Complete dielectric isolation by highly selective and self-stopping formation of oxidized porous silicon," Applied Physics Letters, vol. 42, no. 4, pp. 386-88, Feb. 1983.						
	✓ C.E. Hunt, et al., "Thinning of Bonded Waters: Etch-Stop Approaches", Extended Abstracts, Elect. Chem. Soc. 1 <sup>st</sup> Symp., pp. 165-73 (1991)						
	✓ K. Imai, "A New Dielectric Isolation Method Using Porous Silicon," Solid State Electronics, vol. 24, pp. 159-64, 1981.						
G	✓ K. Imai et al., "Crystalline Quality of Silicon Layer Formed by FIPOS Technology," J. of Crystal Growth 63, 547-553 (1983)						
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OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)			
G	✓	T. Ito et al. "Porous Silicon Crystal Prepared by Anodization", <u>Applied Physics</u> (Japanese) vol. 57 no. 11 (1988) (no translation)	
	✓	V. Labunov, "Heat Treatment Effect on Porous Silicon," <u>Thin Solid Films</u> , 137 (1986) 123-134	
	✓	W.P. Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review", J. Electrochem. Soc., vol. 138, No. 1, pp. 340-47 (1991)	
	✓	Kazutoshi Nagano, et al., "Oxidized Porous Silicon and It's Application", Semiconductor Research Lab Matsushita Electric Industrial Co., Ltd. (no translation)	
	✓	Nikkei Microdevice, pp. 76-77 (1994) (with translation)	
	✓	K. Ogasawara, et al., "Enhancement of Electroluminescence from n-Type Porous Silicon and Its Photoelectrochemical Behavior", J. Electrochem. Soc., vol. 142, no. 6, pp.1874-79 (1995)	
	✓	M. Ohnishi, et al., "New Type Structures Of A-Si Solar Cell Submodules Fabricated By Microscopic Hole Spacing Technique", Record of the Photovoltaic Specialist Conference, Kissimimee, May 21-25, 1990, vol. 2, No. Conf. 21, pp. 1394-1399, May 21, 1990.	
	✓	Patent Abstracts of Japan, vol. 18, No. 066 (E-1501), Feb. 3, 1994.	
	✓	V. Raineri, et al., "Silicon-on-insulator produced by helium implantation and thermal oxidation", Appl. Phys. Lett. 66(26), 3653-3656 (June 1995)	
	✓	Sato, Extended Abstracts, Elect. Chem. Soc., vol. 94-1, pp. 705-06 (1994).	
	✓	H. Tayanaka, et al., "Thin-Film Crystalline Silicon Solar Cells Obtained by Separation of a Porous Silicon Sacrificial Layer" 2d World Conf. and Exhibition on Photovoltaic Solar Energy Conversion (1998)	
	✓	T. Unagami, "Formation Mechanism of Porous Silicon Layer by Anodization in HF Solution," Journal of the Electrochemical Society, vol. 127, no. 2, pp. 476-83, Feb. 1980.	
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	✓	T. Yasumata, et al., "Ultrathin Si films grown epitaxially on porous silicon", Applied Surface Science, vol. 48/49, pp. 414-18, May 1991.	
G	✓	T. Yonehara et al., "Epitaxial layer transfer by bond and etch back of porous Si", <u>Appl. Phys. Lett.</u> 64(16), 2108-2110 (1994)	
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
G		5-217981	8/27/93	Japan			Abstract
G		5-217827	8/27/93	Japan			Abstract
G		0 553 861 A1	8/04/93	Europe			
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